**IN THE CLAIMS**:

*This listing of claims will replace all prior versions and listings of claims in the application*

**Listing of Claims**:

1-14. (Cancelled)

15. (Currently amended) A light-emitting diode comprising:

a substrate made of group III-V nitride semiconductor;

a first n-type semiconductor layer containing indium and formed over a main surface of the substrate;

a light-emitting layer formed over the first n-type semiconductor layer;

a second n-type semiconductor layer formed between the substrate and the first n-type semiconductor layer;

a third n-type semiconductor layer formed between the first n-type semiconductor layer and the light-emitting layer; and

a fourth n-type semiconductor layer formed between the first n-type semiconductor layer and the light-emitting layer, the fourth n-type semiconductor layer being directly formed on the third n-type semiconductor layer.

16. (Previously presented) The diode of claim 15,

wherein the fourth n-type semiconductor layer is made of a compound whose general formula is represented by $Al_eGa_{1-e}N$ ($0 \leq e < 1$).

17. (Previously presented) The diode of claim 16,

wherein the fourth n-type semiconductor layer is a cladding layer.

18. (Previously presented) The diode of claim 17,

wherein the cladding layer has a thickness of 5 to 200 nm inclusive.

19. (Cancelled)

20. (Currently amended) An illuminating device comprising multiple light-emitting diodes,

wherein the diodes including:

a substrate made of group III-V nitride semiconductor;

a first n-type semiconductor layer containing indium and formed over a main surface of the substrate; [[and]]

a light-emitting layer formed over the first n-type semiconductor layer;

a second n-type semiconductor layer formed between the substrate and the first n-type semiconductor layer;

a third n-type semiconductor layer formed between the first n-type semiconductor layer and the light-emitting layer; and

a fourth n-type semiconductor layer formed between the first n-type semiconductor layer and the light-emitting layer, the fourth n-type semiconductor layer being directly formed on the third n-type semiconductor layer.

21. (Cancelled)

22. (New) The diode of claim 15, wherein the third n-type semiconductor layer is a contact layer on which a n-side electrode is formed.

23. (New) The illuminating device of claim 20, wherein the third n-type semiconductor layer is a contact layer on which a n-side electrode is formed.

24. (New) The diode of claim 15, wherein the first n-type layer is a monolayer.

25. (New) The diode of claim 20, wherein the first n-type layer is a monolayer.